


WESTCODE
SEMICONDUCTORS

 Technical
 Publication
DF 46
 ISSUE 2
 May, 1989

Fast Recovery Stud-Base Diode Type PCN/PCR046

 45 amperes average: up to 400 volts V_{RRM}
Ratings (Maximum values at T_j 150°C unless stated otherwise)

RATING	CONDITIONS	SYMBOL	
Average forward current	Half sinewave 100°C case temperature	I _{F(AV)}	45A
R.M.S. current		I _{F(RMS)}	118A
D.C. forward current		I _F	118A
Peak one-cycle surge non-repetitive	10m.s. sine pulse { 60% V _{RRM} re-applied max. V _{RM} ≤ 10 Volts	I _{FSM (1)} I _{FSM (2)}	650A 750A
Maximum surge I ² t	10m.s. sine pulse { 60% V _{RRM} re-applied max. V _{RM} ≤ 10 Volts	I ² t (1) I ² t (2)	2113A ² s 2800A ² s
	3m.s. sine pulse V _{RM} ≤ 10 volts	I ² t (3)	2080A ² s
Operating temperature range		T _{case}	-55 + 150°C
Storage temperature range		T _{stg}	-55 + 150°C

Characteristics (Maximum values at T_j 150°C unless stated otherwise)

CHARACTERISTIC	CONDITIONS	SYMBOL	
Peak forward voltage drop	At 135A I _{FM}	V _{FM}	1.56V
Forward conduction threshold voltage		V _O	1.15V
Forward conduction slope resistance		r	3.05mΩ
Peak reverse current	V _{RM} = V _{RRM} (max.)	I _{RRM}	15mA
Thermal resistance	Junction to case	R _{th(j-c)}	0.8°C/W
	Case to heatsink	R _{th(c-hs)}	0.1°C/W
Reverse recovered charge	I _{FM} = 100A, di/dt = 25 A/μs V _{RM} = 50V	Q _{rr}	4.5μC
Reverse recovery time		t _{rr}	0.9μs

VOLTAGE CODE →	02	04				
*Repetitive voltage V _{RRM}	200	400				
Non-repetitive voltage V _{RSM}	300	500				

*Maximum heatsink to free air thermal resistance for which repetitive voltage ratings apply is 7.5°C/W

Ordering Information (Please quote device code as explained below — 10 digits)

S	M	● ●	P	C	●	0	4	6
FIXED BASIC CODE	VOLTAGE CODE (see above)		FIXED OUTLINE CODE		BASE POLARITY N = cathode R = anode		FIXED TYPE CODE	

 Typical code: SM04PCN046 = 400 V_{RRM} stud-base diode with stud cathode

NOTES ON OPERATION

1. For rectangular wave operation, allowance must be made with regard to the maximum permissible case temperature for both the heating caused by the average reverse switching dissipation and the rise in junction temperature per reverse power pulse. Failure to correct for both average and peak temperature rises could result in the failure of the device to withstand the full reverse voltage which is assumed to be applied at the instant of junction recovery.

Allowance may be made for average and peak reverse switching power dissipation as follows:

$$T_{CASE(2)} = T_{CASE(1)} - (E/\text{pulse/volt}) f \cdot V_{RRM} R_{th(J-C)} - \Delta T_J/\text{volt} V_{RRM}$$

where: $T_{CASE(1)}$ is the maximum permissible case temperature for zero reverse losses.

$T_{CASE(2)}$ is the maximum permissible case temperature when allowance for reverse

switching losses has been made.

$E/\text{pulse/volt}$ is the reverse energy (in joules) in the recovery period per volt of reverse applied voltage.

f is the frequency of operation in Hz

V_{RRM} is the repetitive peak reverse voltage

$\Delta T_J/\text{volt}$ is the junction temperature rise in deg. C per volt of reverse applied voltage per reverse recovery pulse

$R_{th(J-C)}$ is $0.8^\circ\text{C}/\text{W}$

2. For sinusoidal operation, the same derating expression may be used, and will offer a considerable safety factor. The commutation rate of forward current may be taken as that obtaining at the instant at which the forward current passes through zero.

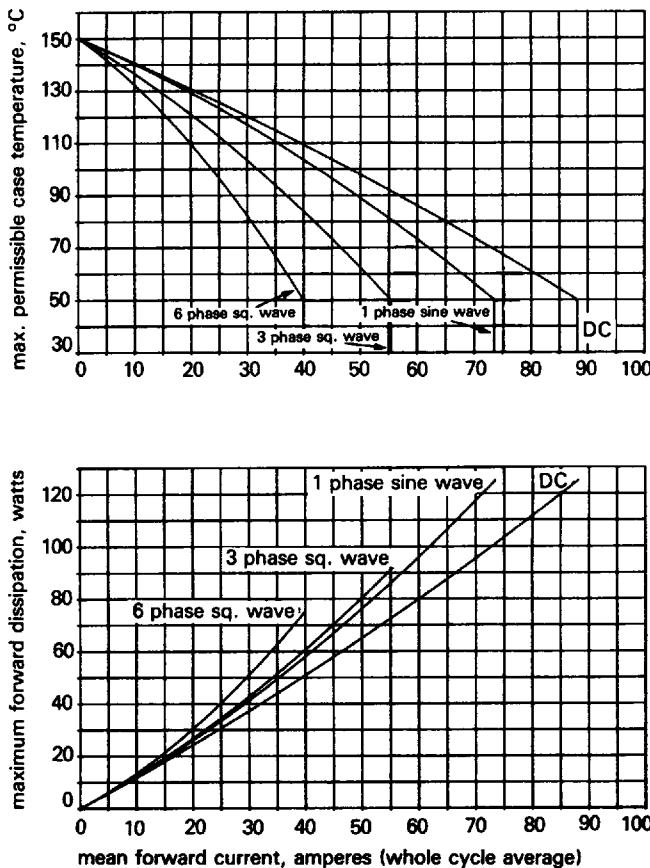


Figure 1. Dissipation and case temperature v. current, 50Hz

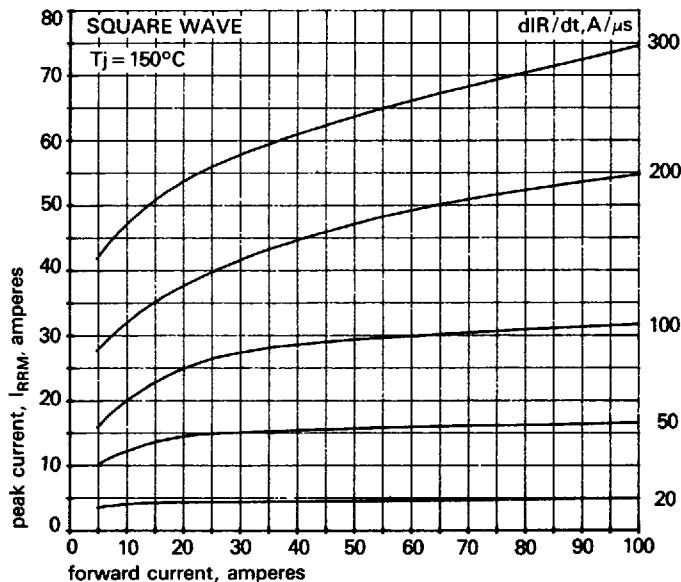


Figure 2. Maximum peak reverse recovery current v. forward current

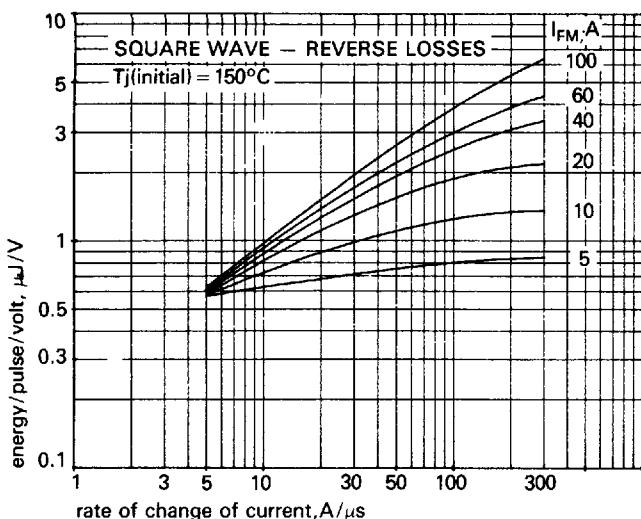


Figure 3. Max. energy/pulse/volt v. rate of change of reverse current

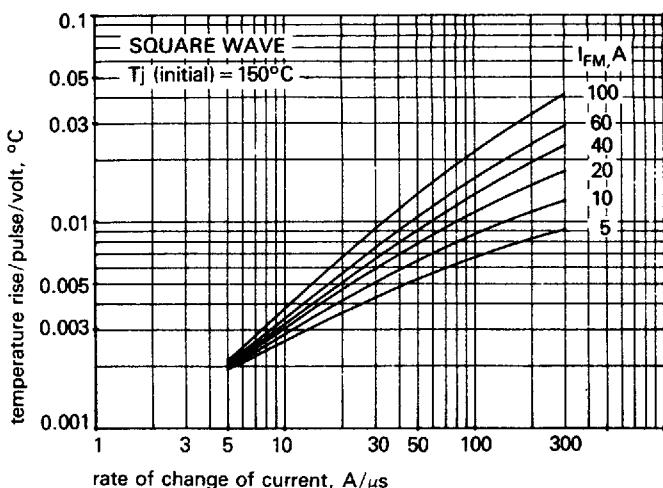


Figure 4. Junction temperature rise/pulse/volt v. rate of change of reverse current

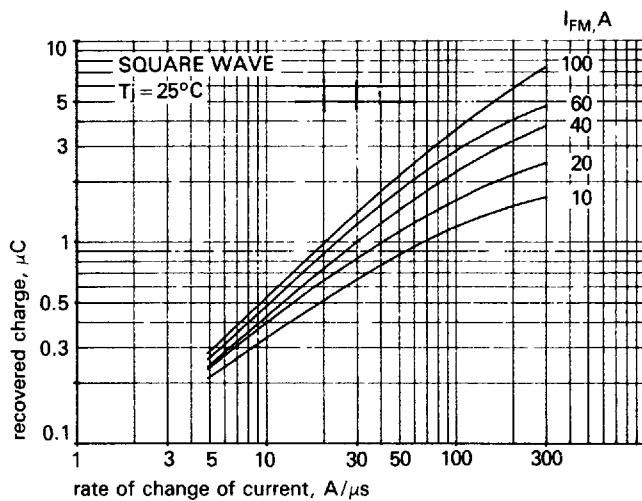


Figure 5. Max. recovered charge v. rate of change of current

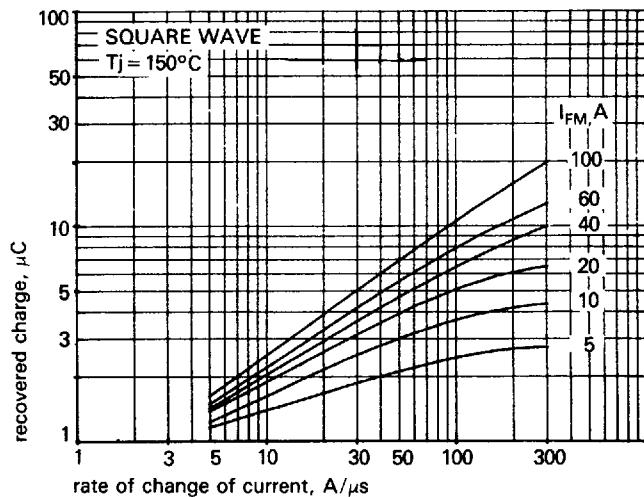


Figure 6. Max. recovered charge v. rate of change of current

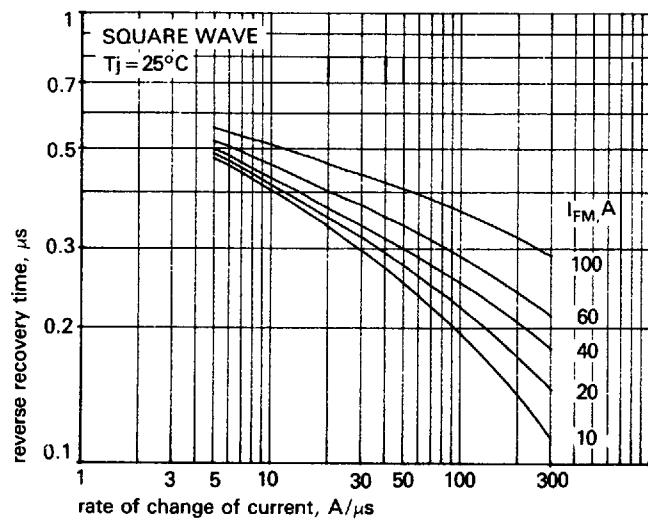


Figure 7. Max. reverse recovery time v. rate of change of current

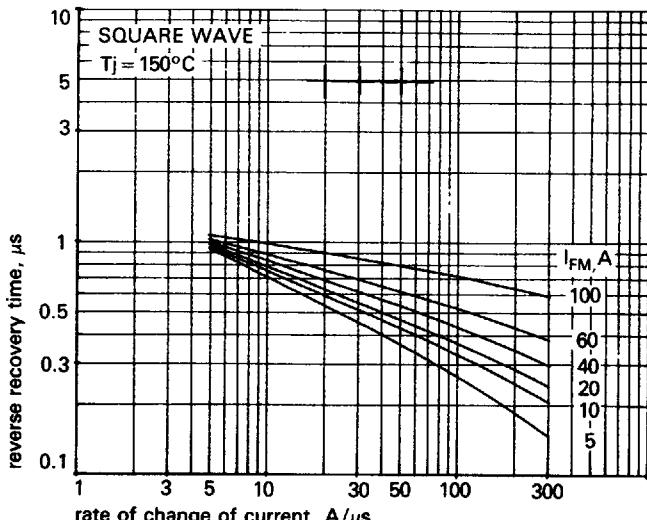


Figure 8. Max. reverse recovery time v. rate of change of current

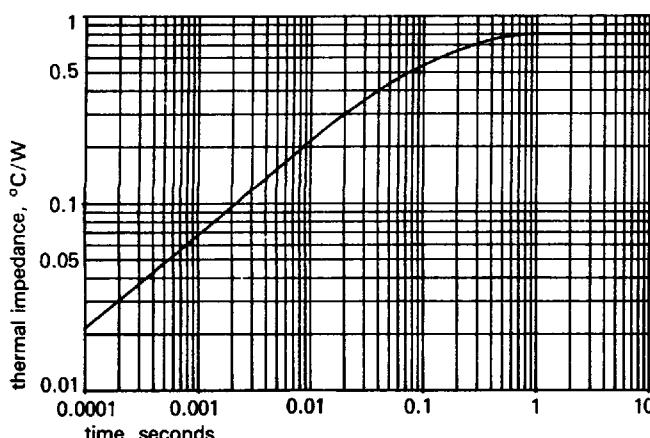


Figure 9. Junction to case transient thermal impedance

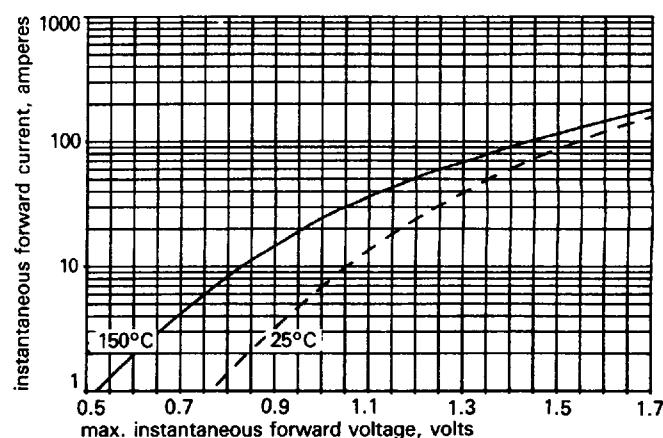


Figure 10. Forward voltage characteristic of limit diode

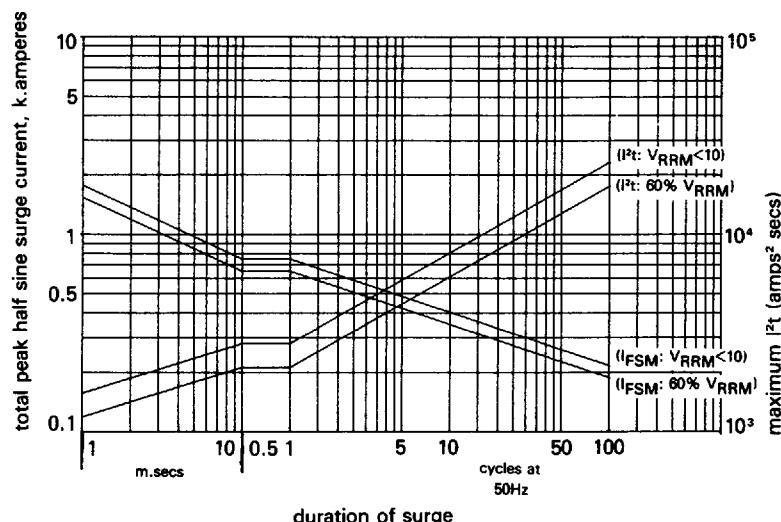
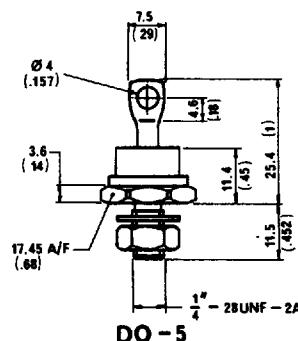


Figure 11. Max. non-repetitive surge current at initial junction temperature 150°C



Dimensions in m.m. (inches)

Mounting torque:

4–4.7 Nm (0.4–0.48 Kgf m)

Threads not to be lubricated

Weight: 20 grams

In the interest of product improvement, Westcode reserves the right to change specifications at any time without notice.

HAWKER

WESTCODE
SEMICONDUCTORS



TELECO

WESTCODE SEMICONDUCTORS LIMITED

P.O. Box 57, Chippenham,

Wiltshire, England SN15 1JL

Telephone: (0249) 444524

Telex: 44751 Telefax: (0249) 659448